

### 40V P-Channel Enhancement Mode MOSFET

-40 V Current

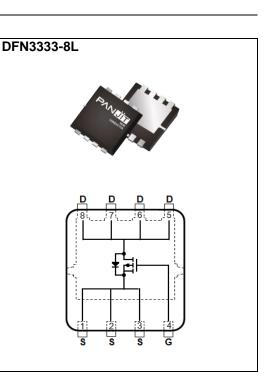
#### Features

Voltage

- $R_{DS(ON)}$ ,  $V_{GS}$ @-10V,  $I_D$ @-10A<12m $\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@-4.5V$ ,  $I_D@-8A<17.5m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultralow on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

- Case : DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.03 grams



#### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

-46 A

PARAMETER Drain-Source Voltage		SYMBOL	LIMIT	UNITS	
		V <sub>DS</sub>	-40		
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 20	V	
Continuous Drain Current	T <sub>C</sub> =25°C	- I <sub>D</sub> -	-46		
	T <sub>C</sub> =100°C		-29	Α	
Pulsed Drain Current <sup>(Note 1)</sup>	T <sub>C</sub> =25°C	I <sub>DM</sub>	-166		
Power Dissipation	T <sub>C</sub> =25°C	D-	59.5	14/	
	T <sub>C</sub> =100°C	PD	23	W	
Continuous Drain Current	T <sub>A</sub> =25°C		-8.8	^	
	T <sub>A</sub> =70°C	I <sub>D</sub>	-7.1	A	
Power Dissipation	T <sub>A</sub> =25°C	D-	2.1	w	
Power Dissipation	T <sub>A</sub> =70°C	Po	1.3		
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	٥C	
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Case	R <sub>θJC</sub>	2.1	•C/W	
	Junction to Ambient	R <sub>θJA</sub>	59.5		

Limited only By Maximum Junction Temperature



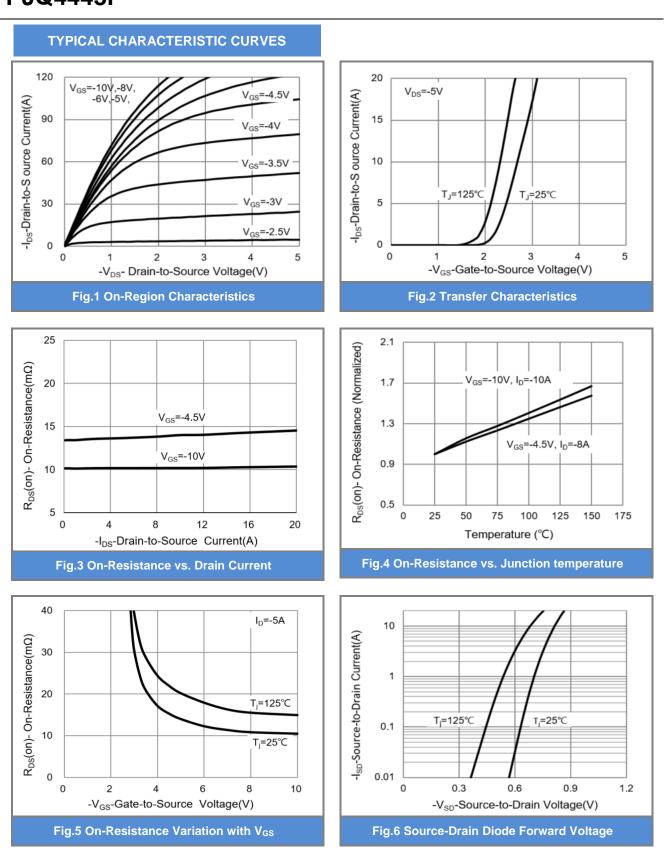
#### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static		I				
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-40	-	-	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1	-1.52	-2.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-10A	-	10	12	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-8A	-	13.5	17.5	
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-40V, V <sub>GS</sub> =0V	-	-	-1.0	uA
Gate-Source Leakage Current	Igss	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic <sup>(Note 6)</sup>						
Total Gate Charge	Qg	V <sub>DS</sub> =-32V, I <sub>D</sub> =-10A, V <sub>GS</sub> =-4.5V <sup>(Note 1,2)</sup>	-	23	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	8.5	-	
Gate-Drain Charge	$Q_{gd}$		-	9	-	
Input Capacitance	Ciss	V <sub>DS</sub> =-25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	2767	-	pF
Output Capacitance	Coss		-	247	-	
Reverse Transfer Capacitance	Crss		-	139	-	
Turn-On Delay Time	td <sub>(on)</sub>	V <sub>DS</sub> =-20V, I <sub>D</sub> =-1A, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω (Note 1,2)	-	23	-	ns
Turn-On Rise Time	tr		-	10	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	135	-	
Turn-Off Fall Time	t <sub>f</sub>		-	50	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			-	-	-46	A
Diode Forward Current	I <sub>S</sub>					
Diode Forward Voltage	V <sub>SD</sub>	Is=-1A, V <sub>GS</sub> =0V	-	-0.7	-1	V

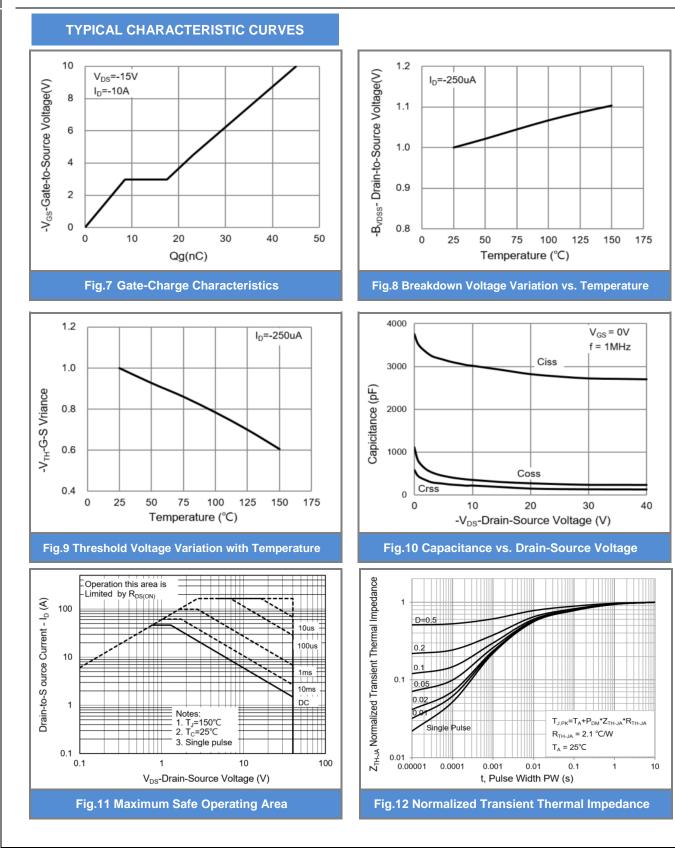
NOTES :

- 1. Pulse width <300us, Duty cycle <2%.
- 2. Essentially independent of operating temperature typical characteristics.
- Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> =25°C.
- 4. The maximum current rating is package limited.
- 5. R<sub>®JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.







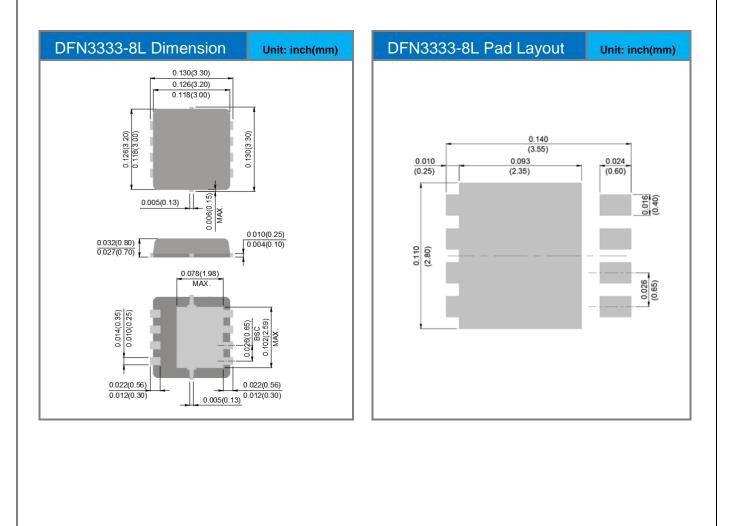




#### Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4443P_R2_00001	DFN3333-8L	5K pcs / 13" reel	4443	Halogen free RoHS compliant

#### **Packaging Information & Mounting Pad Layout**





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